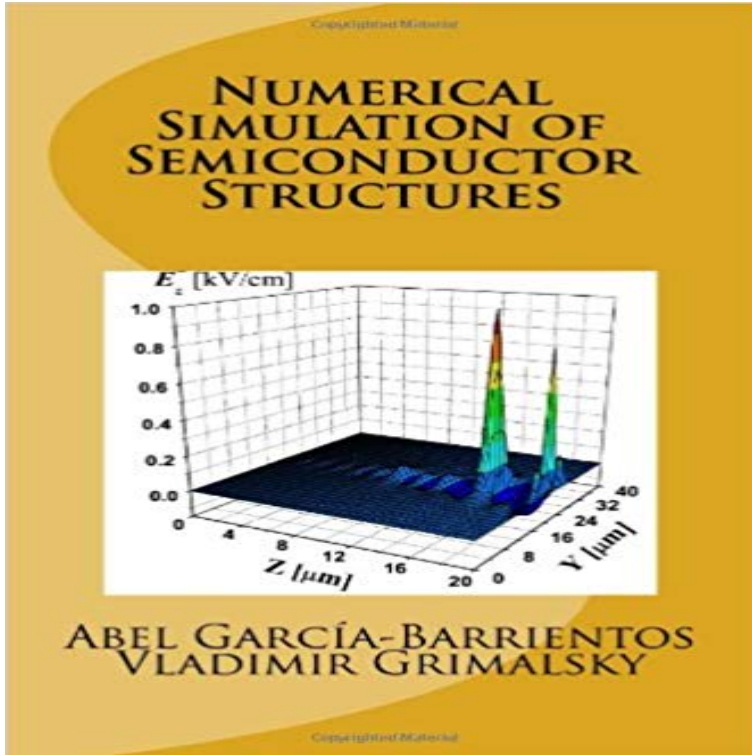


Numerical Simulation of Semiconductor Structures: Numerical Simulation of Semiconductor Structures



The investigation of new materials, devices and techniques to improve the performance of telecommunications, spectroscopy and radar systems applications, has caused that the study of non-stationary effects of space charge in semiconductor structures be a strategy research area in the field of high speed semiconductor devices. Therefore, this book focuses in the study of the non-stationary effects of the space charge in semiconductor structures, where the nonlinear wave interaction in active media may serve to improve the high-frequency performance of semiconductor devices.

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